

General Description

The HXY8205ES is the highest performance trench

N-ch MOSFETs with extreme high cell density,

which provide excellent RDSON and gate charge

for most of the small power switching and

load switch applications. The meet the RoHS and

Product requirement with full function reliability approved.



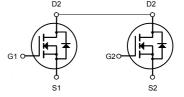
TSSOP-8

General Features

 $V_{DS} = 20V I_{D} = 6A$

 $R_{DS(ON)}$ < 27m Ω @ V_{GS}=4. 5V

 $R_{DS(ON)}$ <37m Ω @ V_{GS}=2. 5V



Application

Battery protection

Load switch

Uninterruptible power supply

Dual N-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
HXY8205ES	TSSOP-8	8205	5000

Absolute Maximum Ratings (TA=25 ℃ unless otherwise noted)

Symbol	Parameter	Limit	Unit	
V _{DS}	Drain-Source Voltage	20	V	
Vgs	Gate-Source Voltage	±12	V	
I _D	Drain Current-Continuous	6	А	
Ірм	Drain Current-Pulsed (Note 1)	25	А	
P _D	Maximum Power Dissipation	1.5	W	
T _J ,T _{STG}	Operating Junction and Storage Temperature Range	-55 To 150	$^{\circ}$	
Reja	Thermal Resistance,Junction-to-Ambient (Note 2)	83	°C/W	



Electrical Characteristics (T_A=25 ℃ unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA 20		21	-	V
Zero Gate Voltage Drain Current	Ipss	V _{DS} =19.5V,V _{GS} =0V	-	-	1	μΑ
Gate-Body Leakage Current	lgss	V _{GS} =±10V,V _{DS} =0V	=0V		±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =250μA	0.5	0.7	1.2	V
		V _{GS} =4.5V, I _D =4.5A	-	21	27	mΩ
Drain-Source On-State Resistance	RDS(ON)	V _{GS} =2.5V, I _D =3.5A	-	27	37	mΩ
Forward Transconductance	grs	V _{DS} =5V,I _D =4.5A	-	10	-	S
Input Capacitance	C _{lss}		-	600	-	PF
Output Capacitance	Coss	V_{DS} =8 V , V_{GS} =0 V , F=1.0 M Hz	-	330	-	PF
Reverse Transfer Capacitance	Crss	F-1.UIVIDZ	-	140	-	PF
Turn-on Delay Time	td(on)		-	10	20	nS
Turn-on Rise Time	tr	V _{DD} =10V,I _D =1A	-	11	25	nS
Turn-Off Delay Time	t _{d(off)}	$V_{GS}=10V_{AB}=12A$ $V_{GS}=4.5V_{AB}=12A$	-	35	70	nS
Turn-Off Fall Time	t _f		-	30	60	nS
Total Gate Charge	Qg		-	10	15	nC
Gate-Source Charge	Qgs	V _{DS} =10V,I _D =6A,	-	2.3	-	nC
Gate-Drain Charge	Q _{gd}	V _{GS} =4.5V	-	1.5	-	nC
Diode Forward Voltage (Note 3)	Vsp	V _{GS} =0V,I _S =1.7A	-	0.75	1.2	V
Diode Forward Current (Note 2)	Is		-	-	1.7	Α

Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- **3.** Pulse Test: Pulse Width ≤ 300μ s, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production



Typical Characteristics

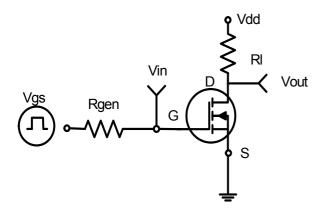


Figure 1:Switching Test Circuit

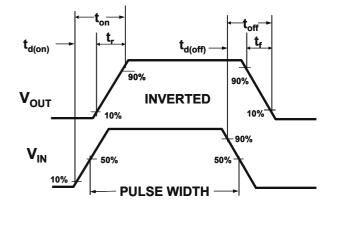


Figure 2:Switching Waveforms

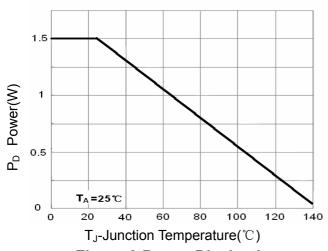


Figure 3 Power Dissipation

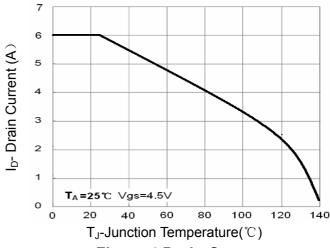


Figure 4 Drain Current

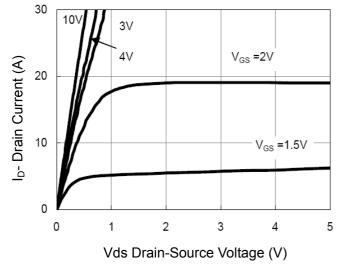


Figure 5 Output Characteristics

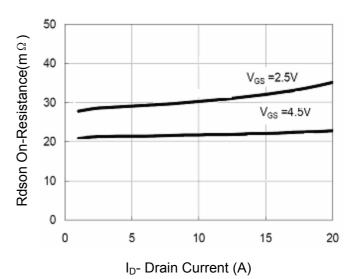


Figure 6 Drain-Source On-Resistance

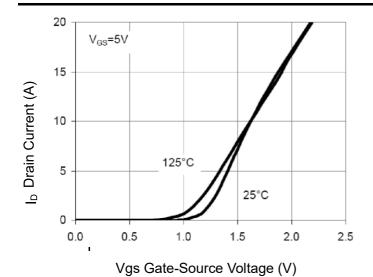
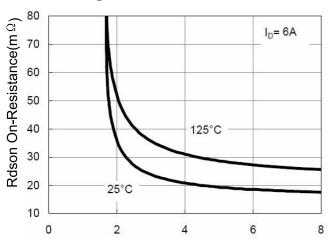


Figure 7 Transfer Characteristics



Vgs Gate-Source Voltage (V) Figure 9 Rdson vs Vgs

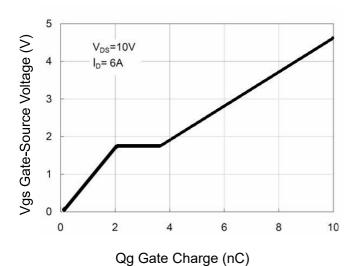
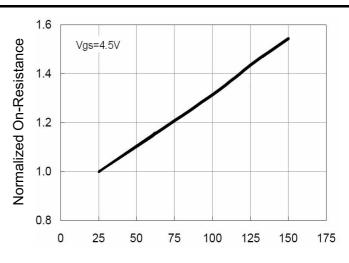
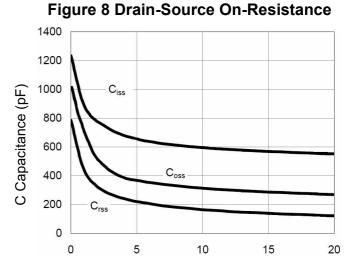


Figure 11 Gate Charge

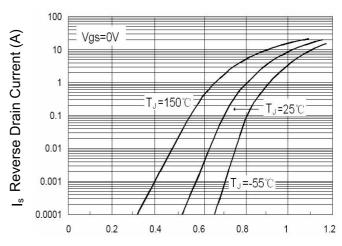


 $\mathsf{T}_{\mathsf{J}} ext{-}\mathsf{Junction}\;\mathsf{Temperature}({}^{\circ}\!\mathbb{C})$



Vds Drain-Source Voltage (V)

Figure 10 Capacitance vs Vds



Vsd Source-Drain Voltage (V)

Figure 12 Source- Drain Diode Forward

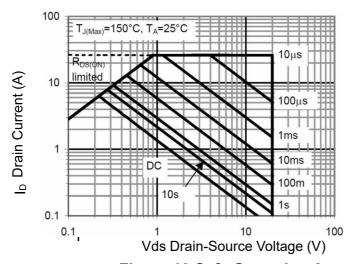


Figure 13 Safe Operation Area

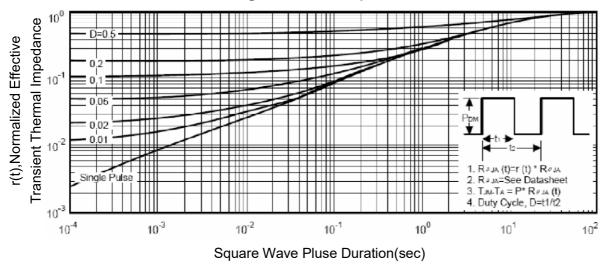
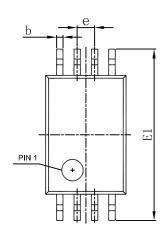
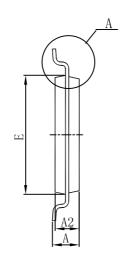


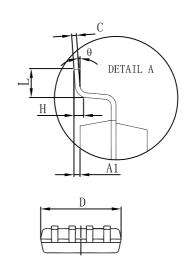
Figure 14 Normalized Maximum Transient Thermal Impedance



TSSOP-8 Package Outline Dimensions







Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min	Max	Min	Max	
D	2.900	3. 100	0. 114	0.122	
Е	4.300	4. 500	0. 169	0.177	
b	0.190	0.300	0.007	0.012	
c	0.090	0.200	0.004	0.008	
E1	6.250	6. 550	0. 246	0.258	
A		1. 200		0.047	
A2	0.800	1. 000	0.031	0.039	
A1	0.050	0. 150	0.002	0.006	
e	0.65 (BSC)		0. 026 (BSC)		
L	0.500	0.700	0. 020	0.028	
Н	0.25(TYP)		0.01(TYP)		
θ	1°	7°	1 °	7°	

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